

MANUFACTURE OF COMPOUND SEMICONDUCTOR WAFER

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Abstract of JP 11204471 (A)

PROBLEM TO BE SOLVED: To achieve high level prevention of oxidation and other modifications occurring after polishing process and to achieve high level removal and cleaning of contamination and adhered particles, by providing an oxidizing process before a finish cleaning including alkali cleaning and after the polishing and organic solvent cleaning. **SOLUTION:** In a polishing process consisting of a polishing step and a subsequent processing step, a wafer surface is polished to mirror face to obtain a mirror finished wafer, and this mirror finished wafer is cleaned in a cleaning process including alkali cleaning to obtain a cleaned mirror wafer. Herein, after the polishing process and before the cleaning process, an oxidizing process is provided, and the mirror finished wafer is oxidized, preferably through ozone oxidation, and more preferably through UV ozone oxidation, so that a oxide film is formed to obtain a mirror wafer with the oxide film, and this mirror wafer with the oxide film is cleaned through the cleaning process, and the removal of oxide film and cleaning are carried out to obtain the cleaned mirror wafer.



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